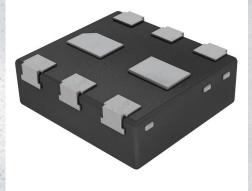


PMDXB950UPEZ Datasheet

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DiGi Electronics Part Number	PMDXB950UPEZ-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PMDXB950UPEZ
Description	MOSFET 2P-CH 20V 0.5A 6DFN
Detailed Description	Mosfet Array 20V 500mA 265mW Surface Mount DF N1010B-6

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMDXB950UPEZ	Nexperia USA Inc.
Series:	Product Status:
	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 P-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
Logic Level Gate	20V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ ld, Vgs:
500mA	1.40hm @ 500mA, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
950mV @ 250µA	2.1nC @ 4.5V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
43pF @ 10V	265mW
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
6-XFDFN Exposed Pad	DFN1010B-6
Base Product Number:	
PMDXB950	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	



PMDXB950UPE

20 V, dual P-channel Trench MOSFET 30 June 2015

Product data sheet

1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance $R_{DSon} = 1.02 \Omega$

3. Applications

- Relay driver
- High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transisto	r		·				
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage	_		-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-500	mA
Static charac	teristics (per transistor)						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -500 mA; T _j = 25 °C		-	1.02	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



PMDXB950UPE

20 V, dual P-channel Trench MOSFET

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	$G1 \xrightarrow{H} \qquad H \xrightarrow{H} \qquad G2$
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1	Transparent top view	S1 S2 017aaa260
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

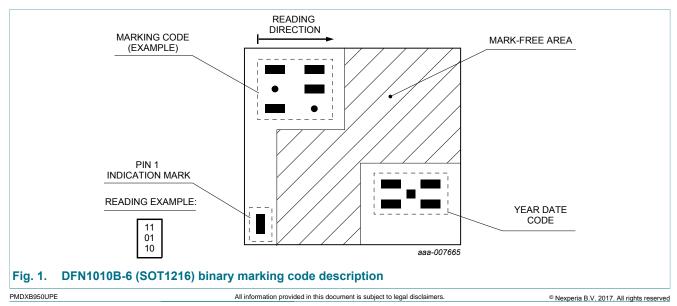
6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMDXB950UPE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216				

7. Marking

Table 4.Marking codes

Type number	Marking code
PMDXB950UPE	10 10 00



PMDXB950UPE

20 V, dual P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

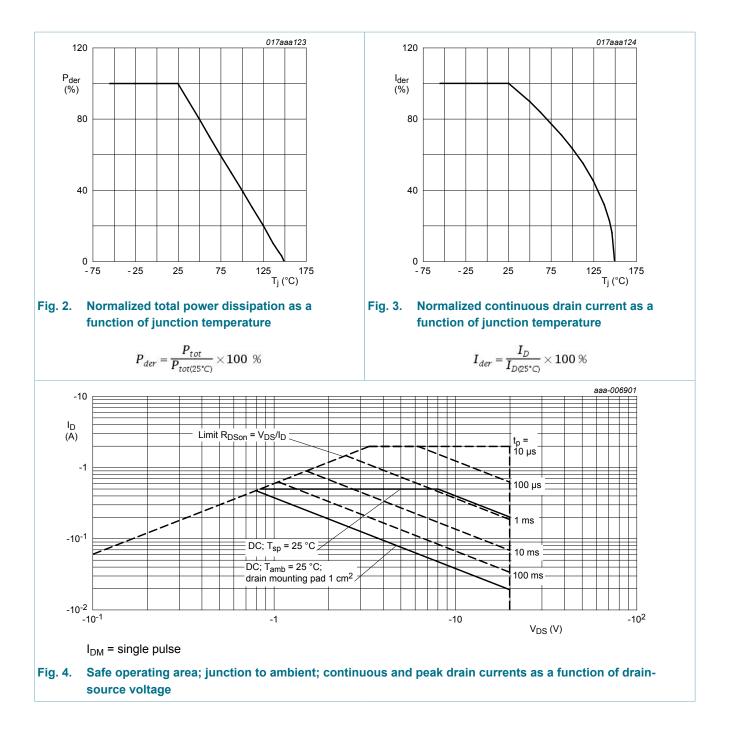
Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	I				
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-500	mA
		V_{GS} = -4.5 V; T_{amb} = 100 °C	[1]	-	-300	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-2	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	380	mW
		T _{sp} = 25 °C		-	4025	mW
Source-dra	in diode	·				,
I _S	source current	T _{amb} = 25 °C	[1]	-	-350	mA
Per device		· · · · · · · · · · · · · · · · · · ·				
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

PMDXB950UPE

20 V, dual P-channel Trench MOSFET



9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	stor						, ,
ui(j-a)	thermal resistance	in free air	[1]	-	410	475	K/W
	from junction to ambient		[2]	-	285	330	K/W

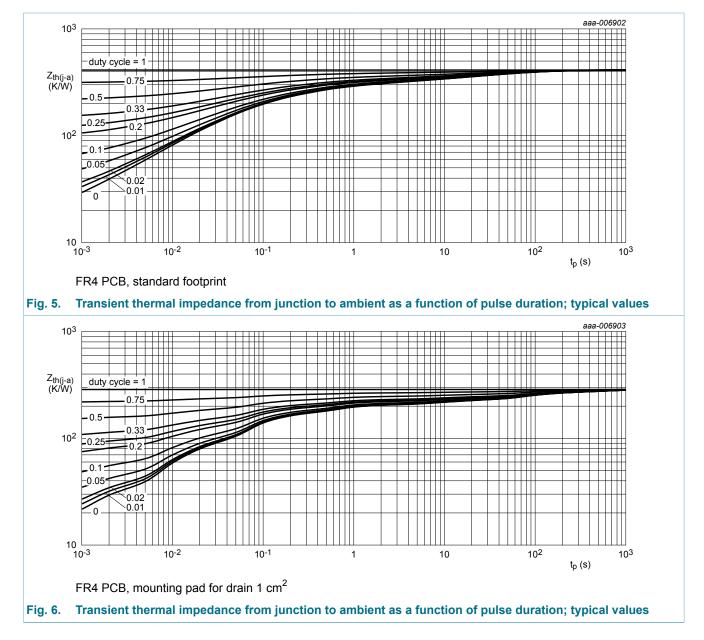
PMDXB950UPE

20 V, dual P-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



PMDXB950UPE

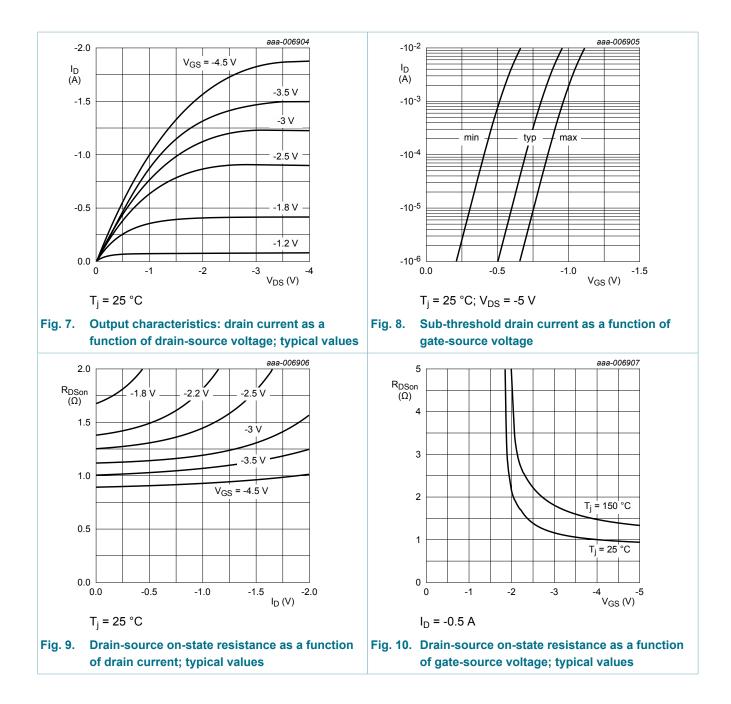
20 V, dual P-channel Trench MOSFET

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -500 mA; T _j = 25 °C	-	1.02	1.4	Ω
	resistance	V _{GS} = -4.5 V; I _D = -500 mA; T _j = 150 °C	-	1.54	2.1	Ω
		V_{GS} = -2.5 V; I _D = -200 mA; T _j = 25 °C	-	1.27	2.2	Ω
		V _{GS} = -1.8 V; I _D = -40 mA; T _j = 25 °C	-	1.7	3.3	Ω
		V _{GS} = -1.5 V; I _D = -10 mA; T _j = 25 °C	-	2.3	5	Ω
		V _{GS} = -1.2 V; I _D = -1 mA; T _j = 25 °C	-	3.5	-	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I _D = -500 mA; T _j = 25 °C	-	480	-	mS
Dynamic ch	aracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V _{DS} = -10 V; I _D = -450 mA;	-	1.19	2.1	nC
Q _{GS}	gate-source charge	V _{GS} = -4.5 V; T _j = 25 °C	-	0.17	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	43	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	14	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_D = -0.45 A; R_L = 22 Ω ;	-	2.3	-	ns
r	rise time	V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ; T_j = 25 °C	-	5	-	ns
t _{d(off)}	turn-off delay time	1	-	13.5	-	ns
t _f	fall time	1	-	6	-	ns
Source-drai	n diode (per transistor)	1	I			
V _{SD}	source-drain voltage	I _S = -115 mA; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

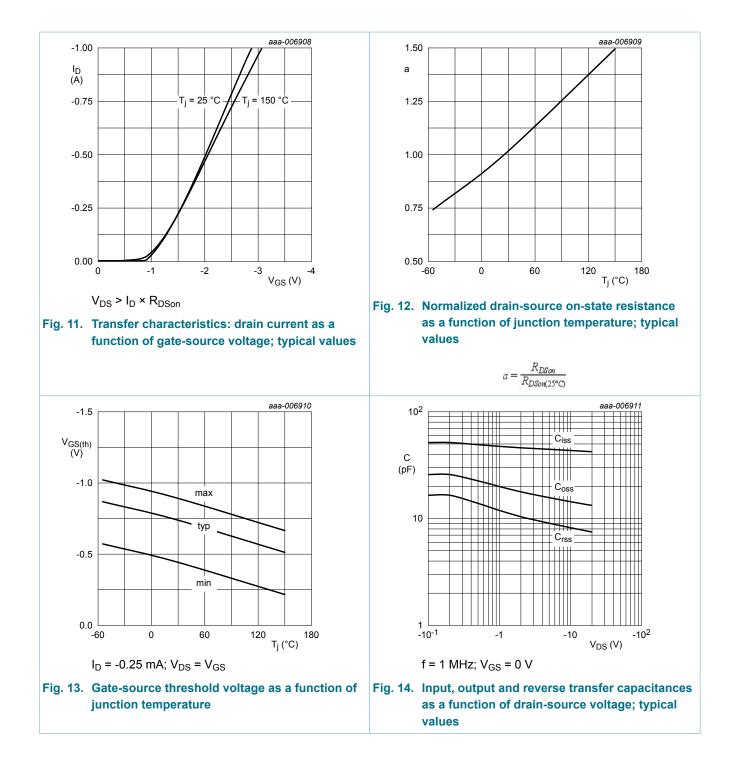
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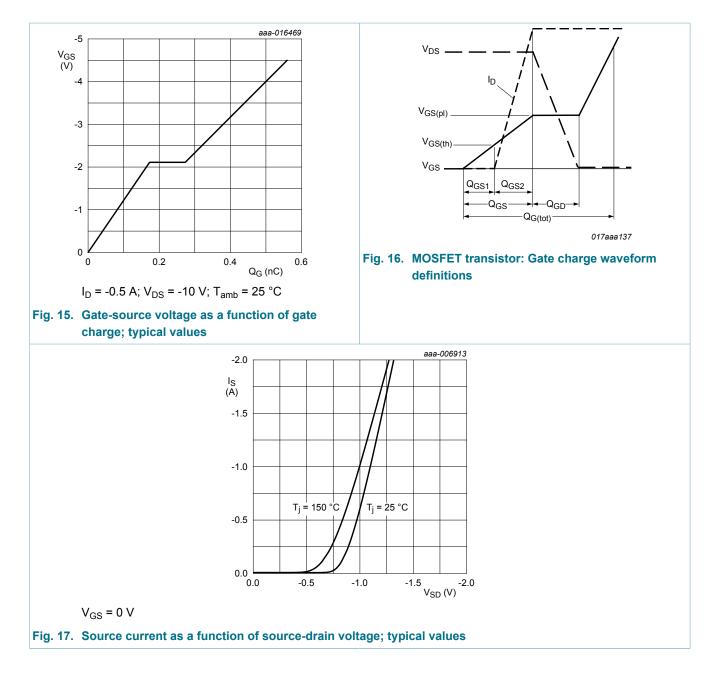
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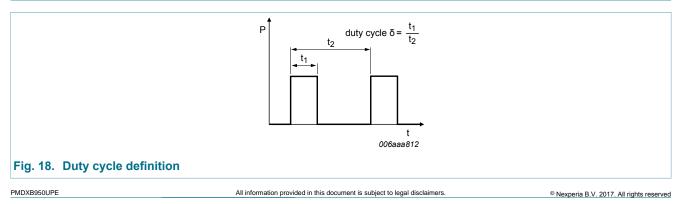


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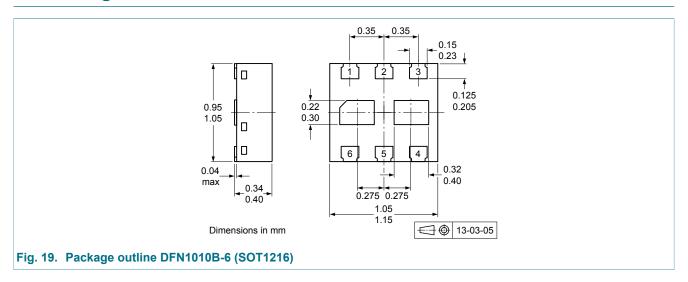
11. Test information



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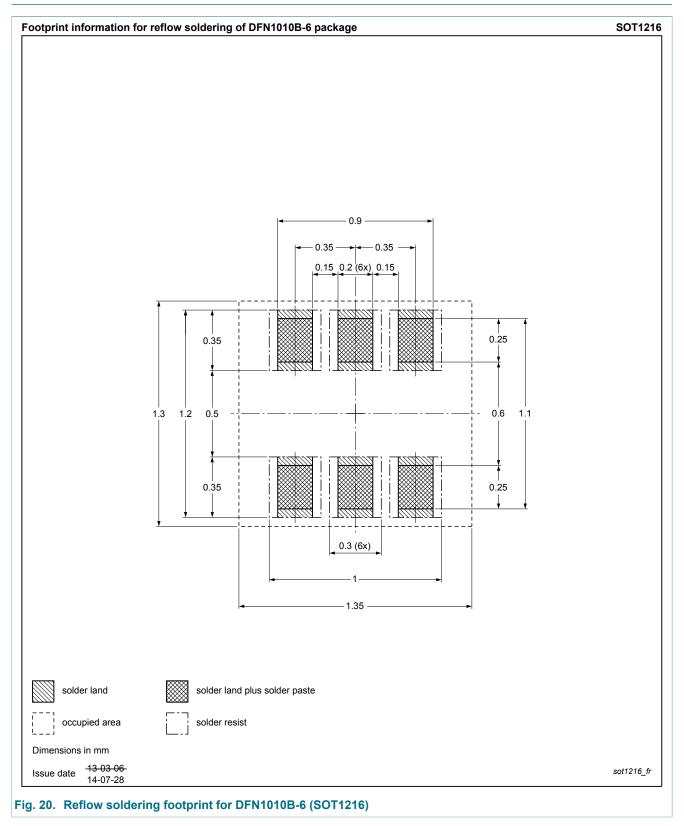
12. Package outline



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20 V, dual P-channel Trench MOSFET

13. Soldering



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20 V, dual P-channel Trench MOSFET

14. Revision history

Table 8. Revision history									
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes					
PMDXB950UPE v.2	20150630	Product data sheet	-	PMDXB950UPE v.1					
Modification: • Change of binary marking code position.									
PMDXB950UPE v.1	20130910	Product data sheet	-	-					

PMDXB950UPE

20 V, dual P-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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